SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

2SC3258

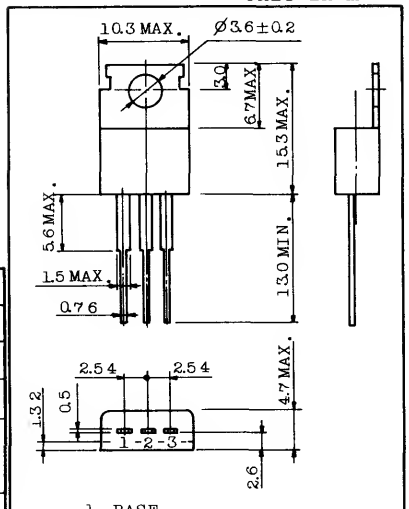
HIGH CURRENT SWITCHING APPLICATIONS.

INDUSTRIAL APPLICATIONS

FEATURES:

. Low Collector Saturation Voltage
  : $V_{CE(sat)}$=0.4V(Max.) at I_C=3A
. High Speed Switching Time : t_{stg}=1.0μs(Typ.)
. Complementary to 2SA1293.

Unit in mm



1. BASE
2. COLLECTOR (HEAT SINK)
3. EMITTER

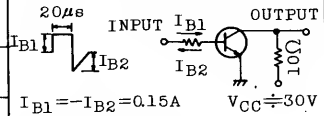
JEDEC	TO-220AB
EIAJ	SC-46
TOSHIBA	2-10A1A

Mounting Kit No. AC75
Weight : 1.9g

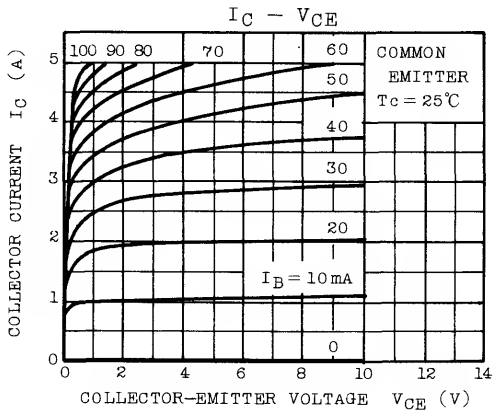
MAXIMUM RATINGS (Ta=25°C)

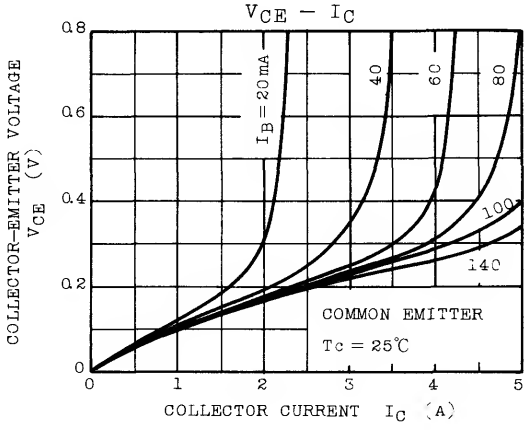
CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	100	V
Collector-Emitter Voltage		V_{CEO}	80	V
Emitter-Base Voltage		V_{EBO}	7	V
Collector Current	DC	I_C	5	A
	Pulse	I_{CP}	8	
Collector Power Dissipation (Tc=25°C)		P_C	30	W
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	-55~150	°C

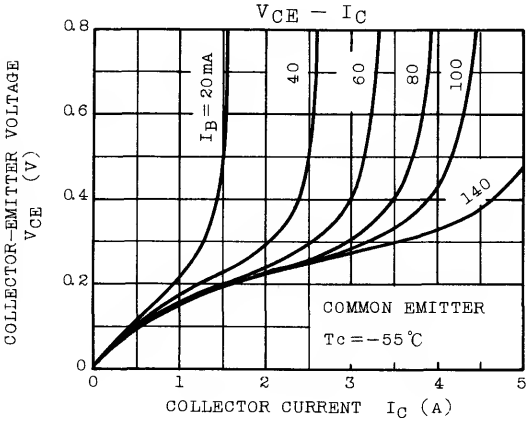
ELECTRICAL CHARACTERISTICS (Ta=25°C)

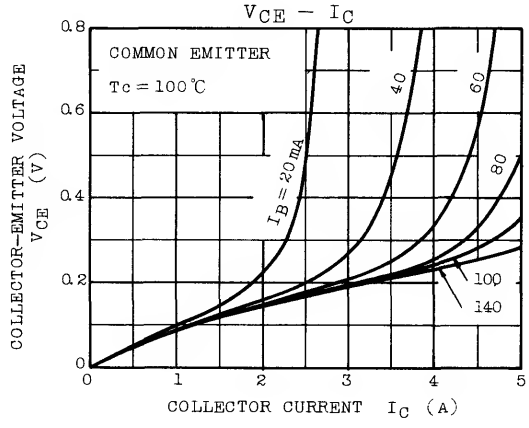
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	V_{CB}=100V, I_E=0	-	-	1	μA
Emitter Cut-off Current		I_{EBO}	V_{EB}=7V, I_C=0	-	-	1	μA
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	I_C=10mA, I_B=0	80	-	-	V
DC Current Gain		$h_{FE(1)}$ (Note)	V_{CE}=1V, I_C=1A	70	-	240	
		$h_{FE(2)}$	V_{CE}=1V, I_C=3A	40	-	-	
Saturation Voltage	Collector-Emitter	$V_{CE(sat)}$	I_C=3A, I_B=0.15A	-	0.2	0.4	V
	Base-Emitter	$V_{BE(sat)}$		-	0.9	1.2	
Transition Frequency		f_T	V_{CE}=4V, I_C=1A	-	120	-	MHz
Collector Output Capacitance		C_{ob}	V_{CB}=10V, I_E=0, f=1MHz	-	80	-	pF
Switching Time	Turn-on Time	t_{on}		-	0.2	-	μs
	Storage Time	t_{stg}		-	1.0	-	
	Fall Time	t_f		-	0.1	-	

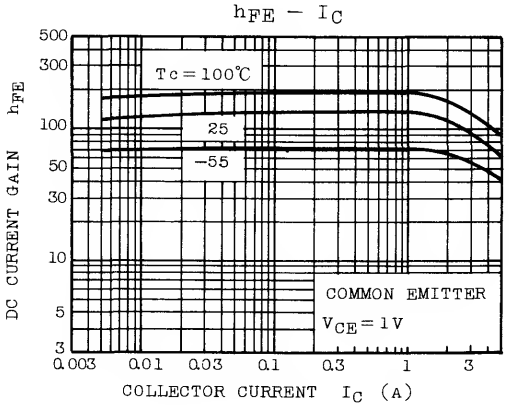
Note : $h_{FE(1)}$ Classification O : 70~140, Y : 120~240

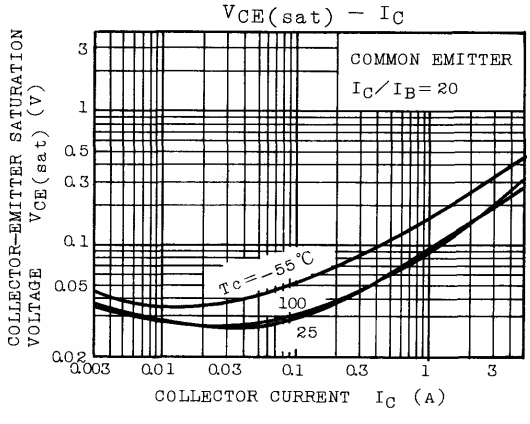

$I_C - V_{CE}$
COLLECTOR CURRENT I_C (A)
COLLECTOR–EMITTER VOLTAGE V_{CE} (V)
100 90 80
70
60
50
40
30
20
0
I_B = 10 mA
COMMON EMITTER
Tc = 25°C


$V_{CE} - I_C$
COLLECTOR–EMITTER VOLTAGE V_{CE} (V)
COLLECTOR CURRENT I_C (A)
I_B = 20 mA
40
60
80
100
140
COMMON EMITTER
Tc = 25°C

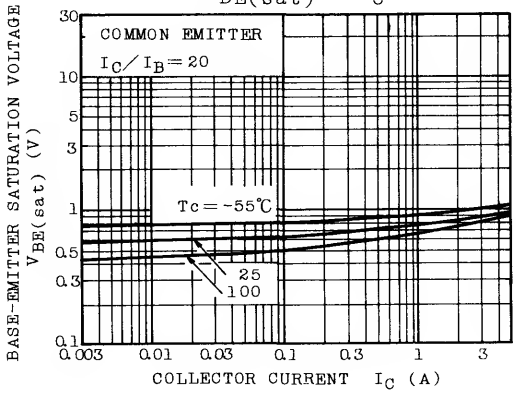

$V_{CE} - I_C$
COLLECTOR–EMITTER VOLTAGE V_{CE} (V)
COLLECTOR CURRENT I_C (A)
I_B = 20 mA
40
60
80
100
140
COMMON EMITTER
Tc = −55°C


$V_{CE} - I_C$
COLLECTOR–EMITTER VOLTAGE V_{CE} (V)
COLLECTOR CURRENT I_C (A)
COMMON EMITTER
Tc = 100°C
I_B = 20 mA
40
60
80
100
140

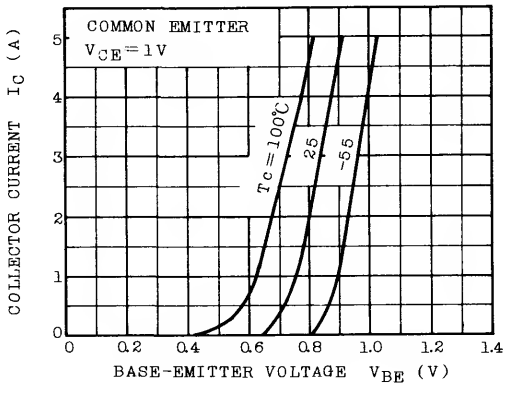

$h_{FE} - I_C$
DC CURRENT GAIN h_{FE}
COLLECTOR CURRENT I_C (A)
Tc = 100°C
25
−55
COMMON EMITTER
V_{CE} = 1V


$V_{CE(sat)} - I_C$
COLLECTOR–EMITTER SATURATION VOLTAGE $V_{CE(sat)}$ (V)
COLLECTOR CURRENT I_C (A)
COMMON EMITTER
I_C / I_B = 20
Tc = −55°C
100
25

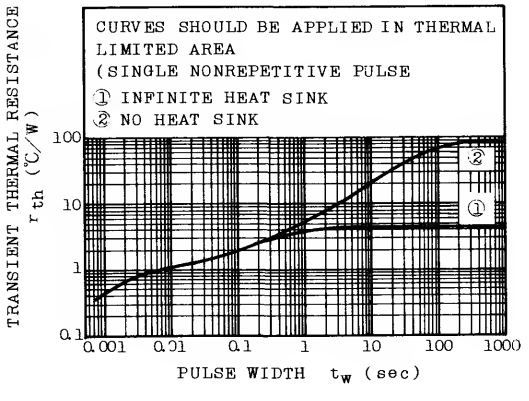
$V_{BE(sat)}$ – I_C



I_C – V_{BE}



r_{th} – t_w



SAFE OPERATING AREA